

Application No. 10/765,056

Amendments to the Specification:

Please replace paragraph [0087] with the following rewritten paragraph:

[0087] Referring to Fig. 7, a TFT 200 includes an approximately rectangular gate electrode film 203a in plan view. Meanwhile, like the gate electrode film 203a, a light shielding film 11aP also includes the shape of a substantially rectangle in plan view. Further, the light shielding film 11aP is not formed in the lower portion of the gate electrode film 203a, i.e., the portion corresponding to a channel region of the semiconductor layer 201a but formed only in the portions corresponding to a source region and a drain region which are located on both sides of the channel region. In other words, the light shielding film 11aP is divided making the portion corresponding to the channel region a boundary. The gate electrode film 203a and the light shielding film 11aP overlap each other in the long side portion of the rectangle as shown in Fig. 7 (refer to H in Figs. 7 and 8). In addition, the degree of overlapping according to the present exemplary embodiment is indicated by the mark L of Fig. 8 when the channel width W of Fig. 7 is approximately 600 ~~μm~~ μm, and the distance L is preferably, for example, about 0.5 ~~μm~~ μm long.

Please replace paragraph [0089] with the following rewritten paragraph:

[0089] The distance between the light shielding film 11aP and the gate electrode film 203a, i.e., the entire thickness D (see Fig. 8) of the basic insulating film 12, the gate insulating film 202, and the semiconductor layer 201a is preferably about 3000 ~~nm~~ nm or less, or more preferably about 2000 ~~nm~~ nm or less, considering the miniaturization of the electro-optical device, the reliable insulation by the basic insulating film 12, the optimal time period of film formation, and the thickness of the semiconductor layer 201a and the gate insulating film 202 for the appropriate operation of the TFT 200. In a variation, the thickness E (see Fig. 8) of the basic insulating film 12 between the light shielding film 11aP and the semiconductor layer 201a is about 3000 nm or less.

Application No. 10/765,056

Please replace paragraph [0090] with the following rewritten paragraph:

[0090] The following effects can be obtained by the light shielding film 11aP thus configured. That is, by overlapping a gate electrode film 203a and a light shielding film 11aP as shown in Figs. 6 or 7 and 8, the possibility is markedly reduced that a crack will be created in the basic insulating film 12, the gate insulating film 202, or the semiconductor layer 201a which is located between them. The reason for obtaining such an effect will be now set forth in conjunction with Figs. 9 to 11. Figs. 9 and 10 are comparative examples corresponding to Figs. 7 and 8 respectively, ~~and Figs. 11(A) and 11(B)~~ and Figs. 11(A) and 11(B) are schematics illustrating how the crack Cr shown in Figs. 9 and 10 is created. Also, various elements shown in Figs. 9 to 11 which perform substantially the same functions as those in Figs. 7 and 8 are indicated by the same reference numerals for convenience of explanation.